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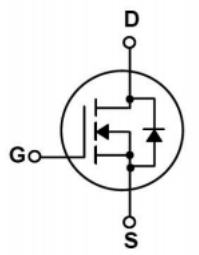

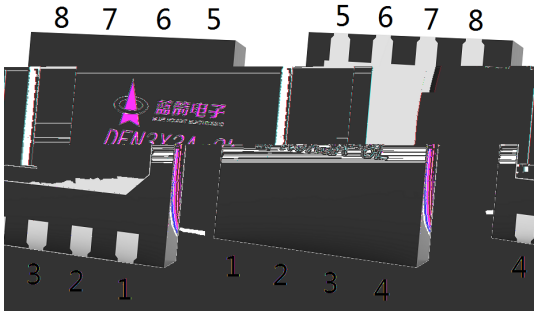

出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	20	V
Drain Current		I_D(Tc=25)	43	A
Drain Current - Pulsed		I_{DM}	107	A
Gate-Source Voltage		V_{GS}	±12	V
Avalanche Current		I_{AS}	12.5	A
Single Pulsed Avalanche Energy		E_{AS}	111	mJ
Power Dissipation		P_D(Tc=25)	28	W
Junction Temperature Range		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	
Maximum Junction-to-Ambient	t≤10s	$R_{\theta JA}$	50	/W
	Steady-State		70	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	4.5	/W

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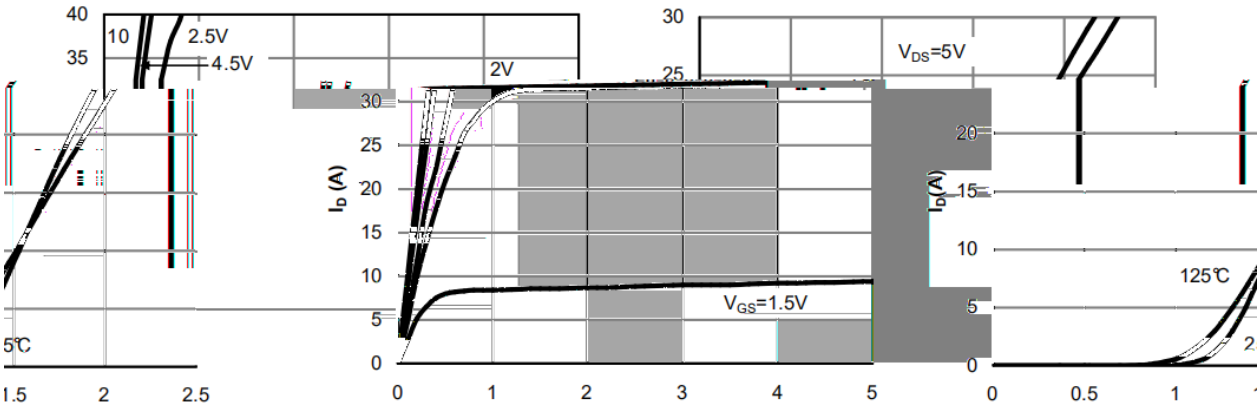
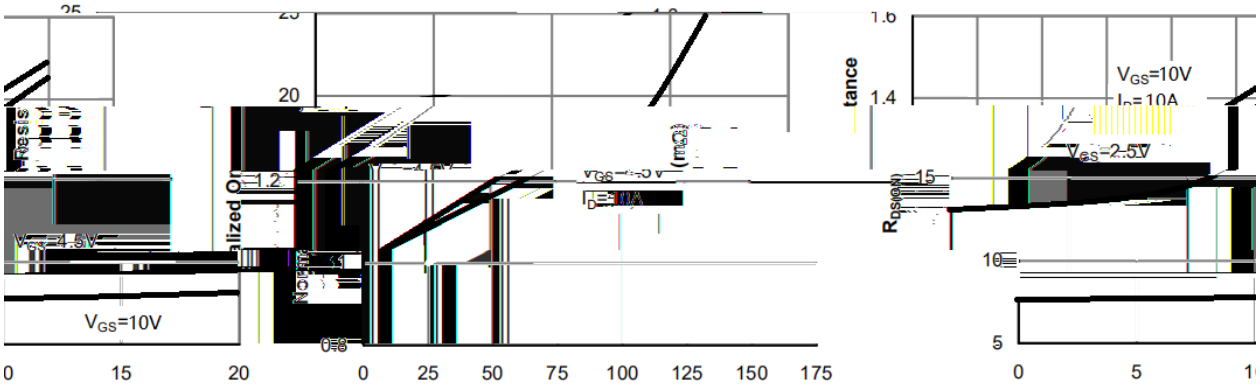


aracteristics

Fig 1: On-Region Characteristics

Figure 2: Transfer Ch

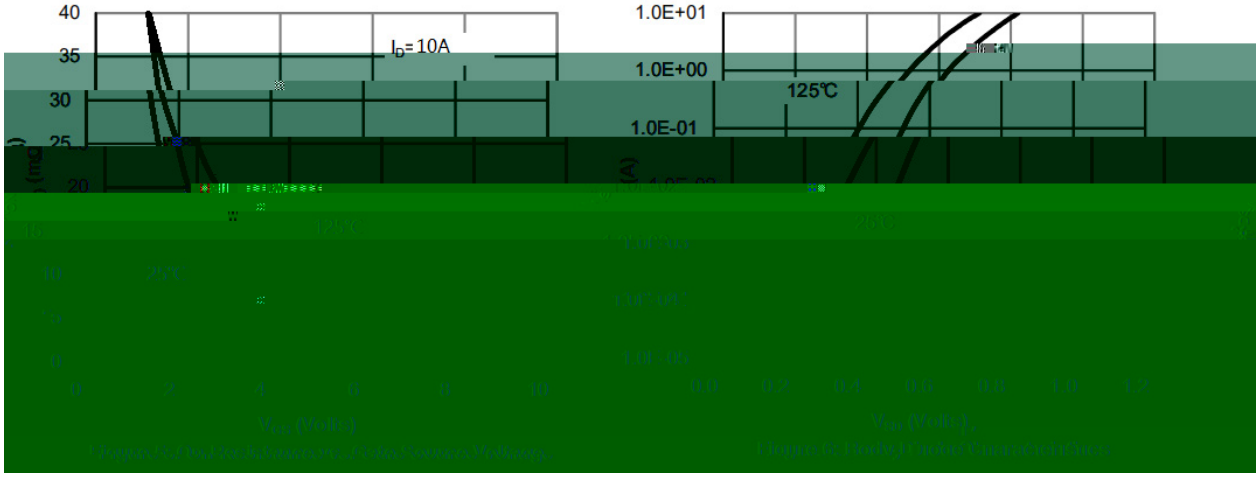


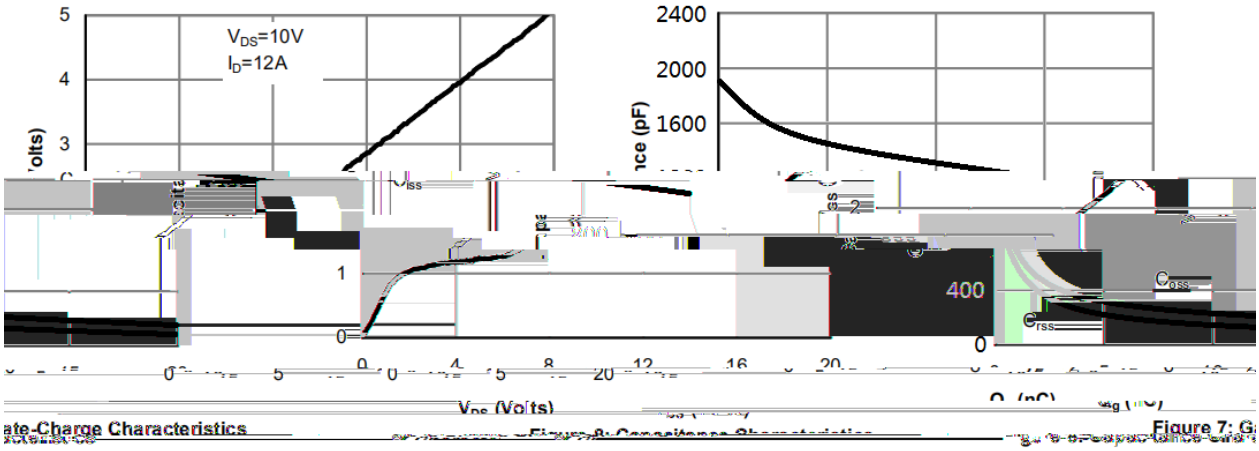
A)
e vs. Drain Current and
oltage

Temperature (℃)

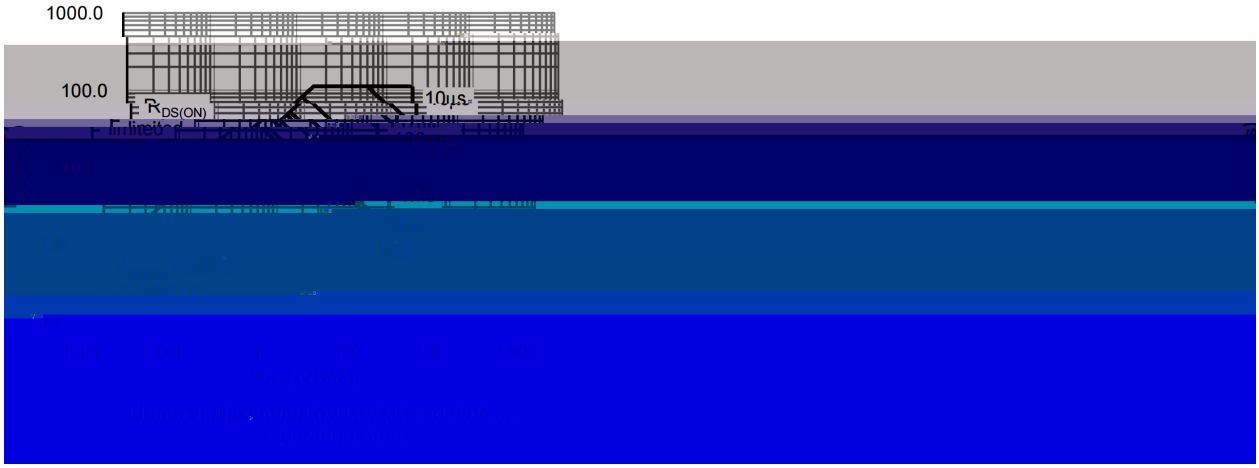
Figure 4: On-Resistance vs. Junction Temperature

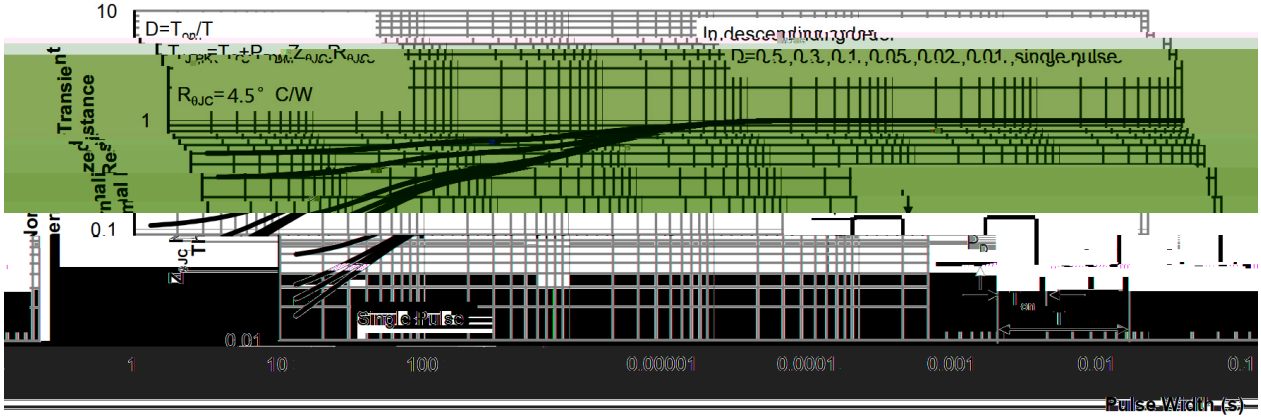
Figure 3: On-Resistanc
Gate V





ate-Charge Characteristics Figure 7: G

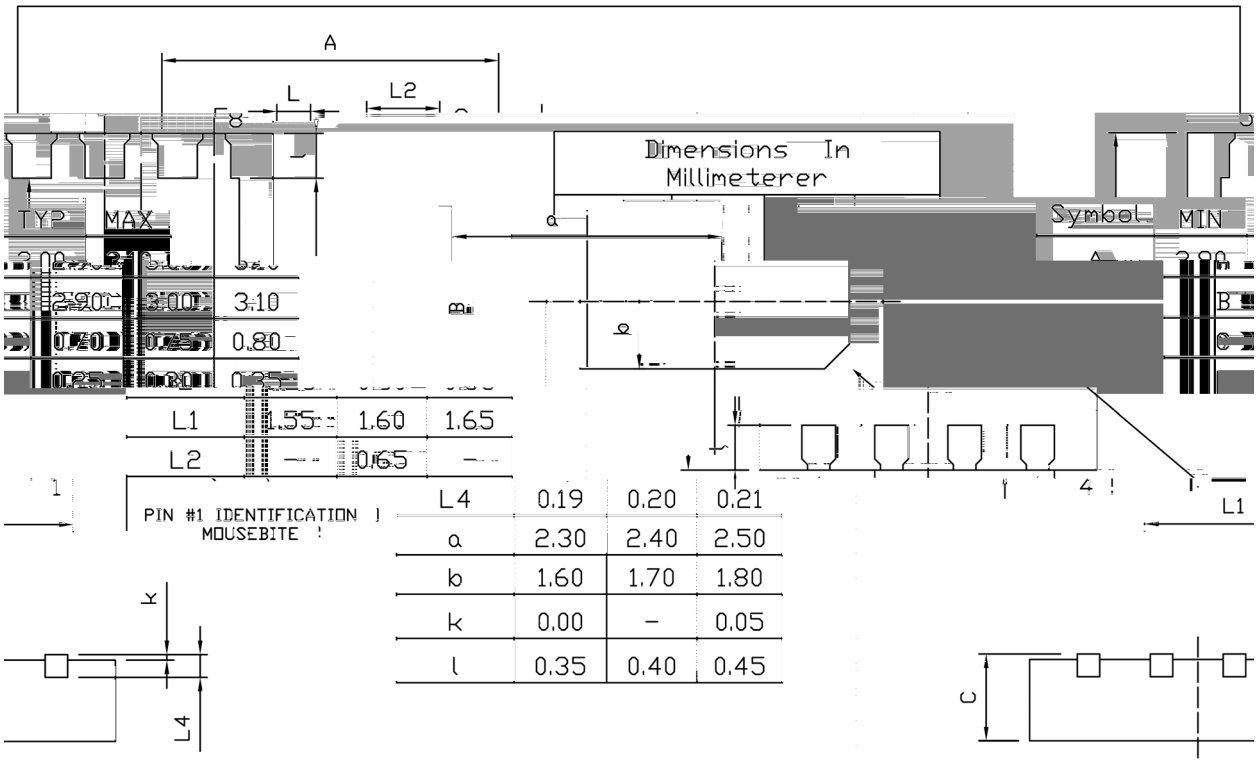




nt Thermal Impedance Figure 10: Normalized Maximum Transie

DFN3X3A-8L

Unit:mm



Symbol	MIN	TYP	MAX
L4	0.19	0.20	0.21
a	2.30	2.40	2.50
b	1.60	1.70	1.80
k	0.00	–	0.05
l	0.35	0.40	0.45

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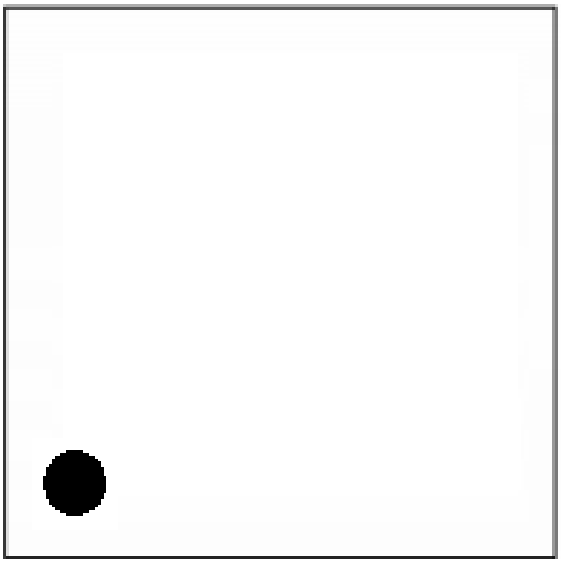
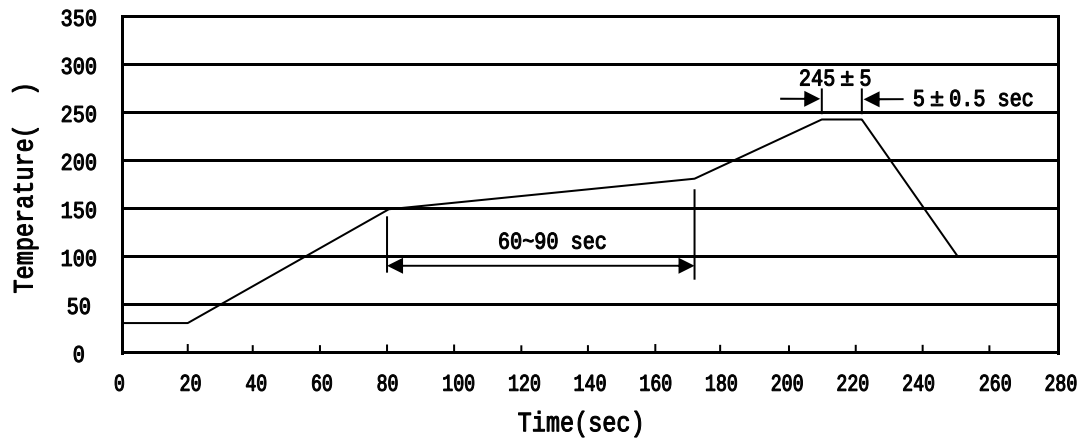


Temperature Profile for IR Reflow Soldering(Pb-Free)



± ± ± ±

± ±

	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
						″		